



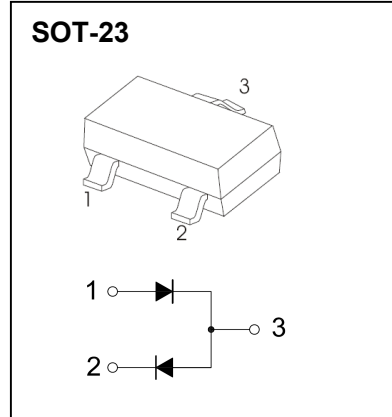
## SOT-23 Plastic-Encapsulate Diodes

### **CMPSH-3S** SCHOTTKY BARRIER DIODE

#### FEATURES

- Fast Switching Speed
- Low Forward Voltage
- Small Plastic Package

MARKING: DA5



#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted )

Symbol	Parameter	Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	30	V
$I_O$	Continuous Forward Current	100	mA
$I_{FRM}$	Peak Repetitive Forward Current	350	mA
$I_{FSM}$	Non-repetitive Peak Forward Current @ $t_p=10\text{ms}$	750	mA
$P_D$	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	286	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	125	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$

#### ELECTRICAL CHARACTERISTICS( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	30			V
Reverse current	$I_R$	$V_R=25\text{V}$			500	nA
		$V_R=25\text{V}, T_a=100^{\circ}\text{C}$			100	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=2\text{mA}$			0.33	V
		$I_F=15\text{mA}$			0.45	
		$I_F=100\text{mA}$			1	
Total capacitance	$C_{tot}$	$V_R=0\text{V}, f=1\text{MHz}$			8	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5	ns